

Patent Attorney's Docket No. <u>015290-457</u>

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of	)		
Jerome S. HUBACEK et al.	) Group Art Unit: 1763		#10A
Application No.: 09/749,916	) Examiner: L. L. Alejandro Mu	ılero	8/12/02
Filed: December 29, 2000	) Confirmation No.: 6834		Mw
For: ELECTRODE FOR PLASMA PROCESSES AND METHOD FOR MANUFACTURE AND USE THEREOF	TC 1/00		<i>2</i> 2
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Assistant Commissioner for Patents Washington, D.C. 20231	L ROOM	2002	OE
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In response to the Official Action dated April 4, 2002, the period for response having been extended until August 4, 2002 by a Petition for a One Month Extension of Time submitted herewith, please amend the above-identified application as follows:

## IN THE CLAIMS:

Please cancel Claims 11-20 without prejudice or disclaimer of the subject matter thereof, replace Claim 1 and add new Claims 21-30 as follows:

1. (Amended) A low resistivity silicon electrode adapted to be mounted in a plasma reaction chamber used in serviconductor substrate processing, comprising:

a silicon electrode having a thickness of at least about 0.3 inch an electrical resistivity of less than 1 ohm-cm, the electrode having an RF driven or electrically grounded surface on one side thereof, the surface being exposed to plasma in the plasma reaction chamber during use of the electrode.